## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Keith E. Kunz, et al.

Docket No:

TI-33676.1

Serial No:

Not Assigned

Conf. No:

**Not Assigned** 

Examiner:

**TBD** 

**Art Unit:** 

**TBD** 

Filed:

07/14/2003

For:

DRAIN-EXTENDED MOS ESD PROTECTION STRUCTURE

## **INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97 & 1.98**

Commissioner For Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

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I hereby certify that the above correspondence is being deposited with the U.S. Postal Service with sufficient postage for "Express Mail Post Office to Addressee" service under 37 CFR 1.10 and is addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on 1-14-03

Ann Trent

Applicants wish to bring to the attention of the Patent and Trademark Office the information noted on the enclosed PTO/SB/08A. A copy of the noted references were provided in connection with the parent application and are therefore not being supplied herewith.

Please charge any shortage in the fees due in connection with the filing of this paper, including extension of time fees, to the deposit account of Texas Instruments Incorporated, Account No. 20-0668, and please credit any excess fees to such Deposit Account. Any further necessary extension of time is hereby requested.

Respectfully summitted,

Peter K. McLarty

**Attorney for Applicants** 

Reg. No. 44,923

Texas Instruments Incorporated P.O. Box 655474, MS 3999 Dallas, TX 75265 (972) 917-5646

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	Substitute for	Form 1449A/PTO		Application Number				
	INFORMATIO	N DISCLOSURE		Fliing Date	07/14/2003			
		BY APPLICANT		First Named Inventor	Keith E. Kunz, et al.			
	STATEMENT	DIAPPLICANI		Group Art Unit				
	(use as many s	heets as necessary)		Examiner Name				
Sheet	1	of	1	Attorney Docket No.	TI-33676.1			

	_			U.:	S. PATENT DOCU	MENTS
Exam.	Cite No.1	U.S. Patent Document		Name of Patentee	Date of Pub.	
		Number	Kind Code <sup>2</sup> (if known)	or Applicant of Cited Doc.	of Cited Doc. (mm-dd-yyyy)	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	AA	4,692,781		Rountree et al.	09/08/1987	
	AB	4,855,620		Duvvury et al.	08/08/1989	
	AC	5,012,317		Rountree	04/30/1991	
	AD	5,907,462		Chatterjee et al.	05/25/1999	
	AE	5,940,258		Duvvury	08/17/1999	
	AF					
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"	AH					
	Al					
	AJ					

	FOREIGN PATENT DOCUMENTS							
Exam. Initials*	Cite No.1	Foreign Patent Document			Name of Patentee	Date of Pub.		
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>2</sup> (if known)	or Applicant of Cited Doc.	of Cited Doc. (mm-dd-yyyy)	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>®</sup>
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		OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS	
Exam. Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
	CA	Rountree et al., "A Process-Tolerant Input Protection Circuit for Advanced CMOS Processes," 1988 EOS/ESD Symposium, pp. 201-05	
	СВ	Duvvury et al., "Substrate Pump NMOS for ESD Protection Applications," 2000 EOS/ESD Symposium, Paper 1A.2.1, pp. 7-17	
	СС	Kunz et al., "5-V Tolerant Fail-safe ESD Solutions for 0.18 um Logic CMOS Process," 2001 ESD/EOS Symposium, September 11, 2001	
	CD		
	CE		
	CF		
	CG		
	СН		
	CI		
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Examiner	Date	i	
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<sup>\*</sup>EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>&</sup>lt;sup>1</sup>Unique citation designation number. <sup>2</sup>Applicant is to place a check mark here if English Translation is attached.